

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (currently amended): A sputtering target that is a perovskite oxide represented by the chemical formula of $\text{Ra}_{1-x}\text{A}_x\text{BO}_{3-\alpha}$, wherein Ra represents ~~a rare earth~~ ~~an element selected from the group~~ consisting of Y, Sc and ~~lanthanoid~~ ~~lanthanide elements~~; A represents Ca, Mg, Ba or Sr; B represents Mn; and $0 < x \leq 0.5$, and wherein the target has a relative density of 95% or more, an average crystal grain size of $100\mu\text{m}$ or less, a resistivity of $10\Omega\text{cm}$ or less, and a purity of 3N or more.

Claims 2-3 (canceled).

Claim 4 (previously presented): A sputtering target according to claim 1, wherein A represents Mg.

Claim 5 (previously presented): A sputtering target according to claim 1, wherein A represents Ba.

Claim 6 (previously presented): A sputtering target according to claim 1, wherein Ra represents Sc.

Claim 7 (previously presented): A sputtering target according to claim 1, wherein Ra represents Ce, Pr, Nd, Sm, Eu, Gd, or Dy.

Claim 8 (previously presented): A sputtering target according to claim 1, wherein the resistivity of the sputtering target is $2\Omega\text{cm}$ or less.

Claim 9 (previously presented): A sputtering target according to claim 8, wherein the relative density of the sputtering target is 98.4% or more

Claim 10 (previously presented): A sputtering target according to claim 9, wherein the average crystal grain size of the sputtering target is $50\mu\text{m}$ or less.

Claim 11 (new): A sputtering target, comprising:

a sintered body sputtering target consisting of a perovskite oxide;

said perovskite oxide represented by the chemical formula of $\text{Ra}_{1-x}\text{A}_x\text{MnO}_{3-\alpha}$,

wherein Ra is an element selected from the group consisting of Sc, Ce, Pr,

Nd, Sm, Eu, Gd and Dy; wherein A is Ca, Mg, Ba or Sr; and wherein

$0 < x \leq 0.5$; and

said sputtering target having a relative density of 95% or more, an average crystal

grain size of $100\mu\text{m}$ or less, a resistivity of $10\Omega\text{cm}$ or less, and a purity of

3N or more.

Claim 12 (new): A sputtering target according to claim 11, wherein said resistivity is $2\Omega\text{cm}$ or less, said relative density is 98.4% or more, and said average crystal grain size is $50\mu\text{m}$ or less.